256Kx16 Static RAM High Speed CMOS, Module

ADVANCE INFORMATION

T-46-23-14

The EDI8M16257C is a 256Kx16 CMOS Static RAM Module consisting of four (4) 128Kx8 CMOS Static RAMs in leadless chip carriers surface mounted onto a multi-layered ceramic substrate. The 128Kx8 RAMs are organized as two banks of 128Kx16 bits each.

Fully asynchronous circuitry requires no clocks or refreshing for operation and provides equal access and cycle times for ease of use.

Military modules, incorporating semiconductor components which are compliant to MIL-STD-883, paragraph 1.2.1, are available.

Features

256Kx16 bit CMOS Static Random Access Memory Module

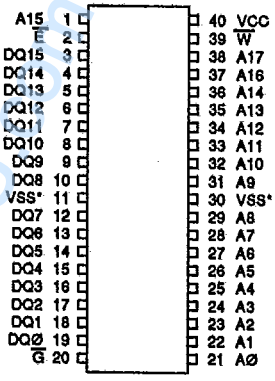
- Access Times 35, 45 and 55ns
- Fully Static, No Clocks
- Inputs and Outputs Directly TTL Compatible

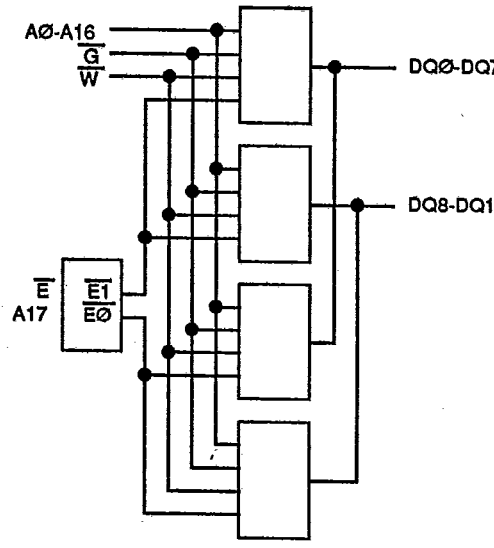
High Density Packaging

- 40 Pin DIP, No. 126

Single +5V (±10%) Supply Operation

Pin Configuration and Block Diagram





Pin Names

AØ-A17	Address Inputs
E	Chip Enable
W	Write Enable
G	Output Enable
DQØ-DQ15	Data Input/ Output
VCC	Power (+5V±10%)
VSS	Ground
NC	No Connection

*Note: Both ground pins (VSS) need to be grounded for proper operation.